
Marina Bujatti

Laurea: 1960

Occupazione

co-fondatrice di Microwave Power InC.

Marina Bujatti frequenta la Scuola di Applicazione per Ingegneri dal 1957 al 1960. Ottiene la **Laurea nel 1960-1961** con una tesi dal titolo: *Progetto di un'apparecchiatura per la misura dei parametri di una ferrite magnetizzata*.

Successivamente ottiene un **dottorato** in Ingegneria Elettrica, sempre presso l'ateneo romano.

È stata **co-fondatrice di Microwave Power InC**, ricoprendo la carica di presidente fino al pensionamento.

PRODUZIONE SCIENTIFICA

Ottiene 4 **brevetti**:

_ 5 giugno 1979: A process for obtaining conductive and resistive elements in microwave circuits in which sequentially a layer of a thin film constituted by a high resistive material is deposited on an insulating substrate, a thin film of conductive material is deposited over the high resistance material, the high resistive film is removed by photoetching from areas which are to constitute resistive elements, a masking material is electrolytically grown on the areas constituting the resistive elements, a thick film of conductive material is electrolytically grown over the entire surface, a protecting material is deposited on areas to constitute conductive elements, the thick film of conductive material is removed by ionic erosion from areas unprotected in the previous step and residual protecting material is removed by differential chemical attack. (Marina Bujatti, Carlo Misiano, Enrico Simonetti)

_ 17 dicembre 1985: A method of making a field effect transistor with a modified metal semiconductor Schottky barrier depletion region wherein a GaAs semiconductive active layer on a semiinsulating substrate is supplied with a pair of ohmic contacts and with a gate or barrier electrode between the ohmic contacts and spaced therefrom so that below the surface of the active layer upon which the barrier electrode and ohmic contacts are supplied, an electron-depletion region is formed between each ohmic contact and the gate or barrier electrode. According to the invention, this surface region is treated by bombardment with nitrogen or by the application of a layer thereto to modify the depth of the depletion region so that this depth beneath the treated surface region will differ from that beneath the gate or barrier electrode. (Marina Bujatti, Antonio Cetronio)

_ 15 maggio 1990: The present invention is directed to a microwave integrated circuit formed on a substrate having via holes for either electrical grounding or heat dissipation or both and more

particularly to a substrate including via holes which are filled with metal. (Marina Bujatti, Franco N. Sechi)

_ 18 giugno 1991: A method of forming a microwave integrated circuit substrate which includes via holes connecting the upper and lower surfaces of the substrate in which the upper end of the via hole is closed by a conductive membrane. (Marina Bujatti, Franco N. Sechi)

Scritti:

1963_ "Measurement of tensor permeability on ferrite", in *Alta Frequenza*

1964_ (con D. Solomini), *Esercizi di elettronica Applicata*, Siderea, Roma

2009_ (con F. Sechi), *Solid-state microwave high-power amplifiers*, Artech House, Boston